KTA1668 TRANSISTOR(PNP)

1.BASE
2.COLLECTOR
3.EMITTER

SOT-89

FEATURES

- High voltage: V_{CEO}=-60V
- High transistors frequency

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-80	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-1	A
P_C	Collector power dissipation	500	mW
T_J,T_{stg}	Operation Junction and Storage Temperature Range	-55~150	℃

ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-0.1mA,I_E=0	-80			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-1mA,I_B=0	-60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-0.1mA,I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-50V,I_E=0			-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-4V,I_C=0			-0.1	μA
DC current gain	h_{FE1}	V_{CE}=-2V,I_C=-50mA	60		320	
	h_{FE2}	V_{CE}=-2V,I_C=-1A	30			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-500mA,I_B=-50mA			-0.7	V
Base-emitter saturation voltage	$V_{B\ E(sat)}$	I_C=-500mA,I_B=-50mA			-1.2	V
Transition frequency	f_T	V_{CE}=-10V,I_C=-50mA, f=100MHz		150		MHz
Collector output capacitance	C_{ob}	V_{CB}=-10V,I_E=0,f=1MHz		12		pF

CLASSIFICATION of h_{FE1}

Rank	O	Y	GR
Range	60-120	100-200	160-320
Marking	JO	JY	JGR